

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising
a first transistor and a second transistor formed on
a semiconductor substrate, wherein a gate side wall of
5 the second transistor has a thickness equal to that of
a gate side wall of the first transistor, wherein each
of the first and second transistors has an inner low
impurity diffusion region and an outer high impurity
diffusion region, and wherein the size of the inner low
10 impurity diffusion region of the second transistor
along the surface of the semiconductor substrate is
larger than that of the inner low impurity diffusion
region of the first transistor.

09973019 101001
FOI 01 610E/660